VDIC
NAND Flash Memory

VDNF32G08XS50XX8V25
USER MANUAL

Version ：A5

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Contents

VDIC-NAND Flash Memory

HIGH-SPEED 3.3V 4G×8bit

1. DESCRIPTION

Offered in 4Gx8bit, the VDNF32G08XS50XX8V25 is a 32G-bit NAND Flash Memory with spare capacity of 128M-bits. The device operates at 3.3V. The I/O pins serve as the ports for address and data input/output as well as command input.

The VDNF32G08XS50XX8V25 device is stacked with eight dies. The operation of each die operates independently. The I/O ports and the control pins (ALE,CLE,#WE,#RE) of all banks in each die are connected.

A program operation can be performed in typical 200μs on the (2K+64)Byte page and an erase operation can be performed in typical 1.5ms on a (128K+4K)Byte block. Data in the data register can be read out at 25ns cycle time per Byte.

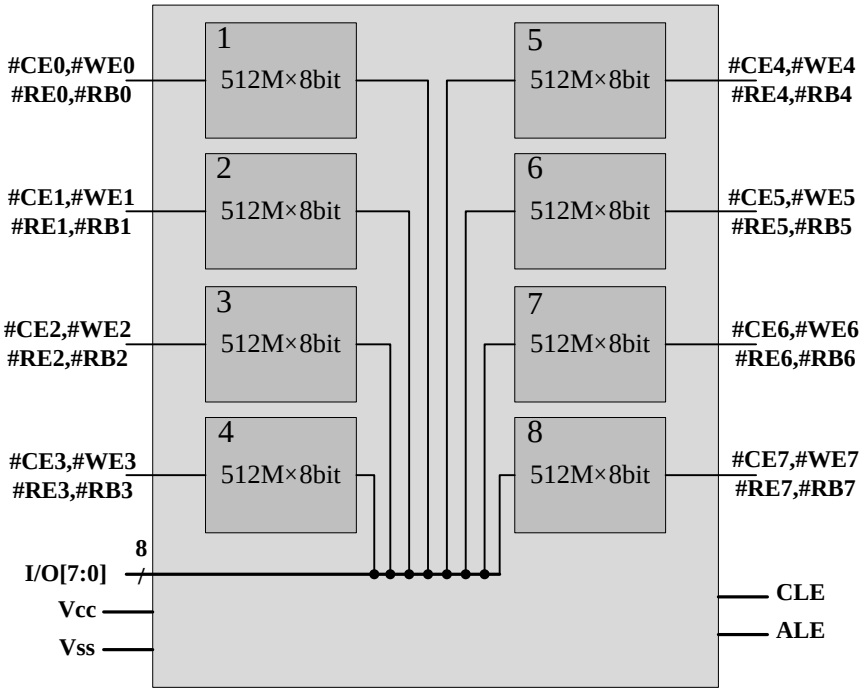
Every die has an on-chip write controller which is used to automate all program and erase functions including pulse repetition, where required, and internal verification and margining of data. Even the write-intensive systems can take advantage of the VDNF32G08XS50XX8V25′s extended reliability of 100K program/erase cycles by providing ECC(Error Correcting Code) with real time mapping-out algorithm.

Its NAND cell provides the most cost-effective solution for the solid state application market. The VDNF32G08XS50XX8V25 is an optimum solution for large nonvolatile storage applications such as solid state data storage and advanced embedded control applications.

2. FEATURES

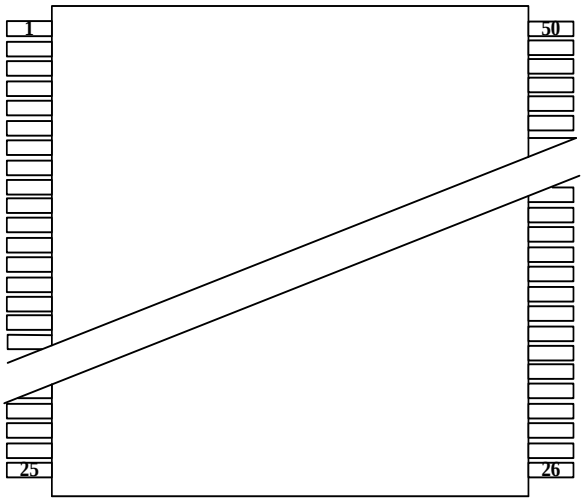
- Voltage Supply
  - 3.3V device: 2.7 ~ 3.6 V
- Organization
  - Memory Cell Array
    - 8Dies x (512M + 8M) Byte x 8 bit
  - Data Register for each bank
    - (2K + 64) Byte x 8bit
- Automatic Program and Erase
  - Page Program for each bank
    - (2K + 64)Byte
  - Block Erase for each bank
    - (128K + 4K)Byte
- Page Read Operation for each bank
  - Page Size
    - (2K + 64)Byte
  - Random Access : 25μs(Max.)
  - Serial Page Access : 25ns(Min.)
- Fast Write Cycle Time
  - Program time : 200μs(Typ.)
  - Block Erase Time : 1.5ms(Typ.)
- Command/Address/Data Multiplexed I/O Port
- Hardware Data Protection
  - Program/Erase Lockout During Power Transitions
- Reliable CMOS Floating-Gate Technology
  - Endurance : 100K Program/Erase Cycles
  - Data Retention : 10 Years
- Command Register Operation
- Intelligent Copy-Back with internal 1bit/528Byte EDC
- Package SOP-50

3. BLOCK DIAGRAM



4. PIN DESCRIPTIONS– SOP-50

Pin Id	Pin #		Pin Id
#RB7	1	50	**#RE7**
#RB6	2	49	**#RE6**
#RB5	3	48	**#RE5**
#RB4	4	47	**#RE4**
#R/B3	5	46	**#RE3**
#R/B2	6	45	**I/O7**
#R/B1	7	44	**I/O6**
#R/B0	8	43	**I/O5**
#RE0	9	42	**I/O4**
#CE0	10	41	**#RE2**
#CE1	11	40	**#RE1**
#CE2	12	39	**VCC**
VCC	13	38	**VCC**
VSS	14	37	**VSS**
#CE3	15	36	**VSS**
#CE4	16	35	**VSS**
CLE	17	34	**#CE5**
ALE	18	33	**I/O3**
#WE0	19	32	**I/O2**
#WP	20	31	**I/O1**
#WE1	21	30	**I/O0**
#WE2	22	29	**#CE7**
#WE3	23	28	**#CE6**
#WE4	24	27	**#WE7**
#WE5	25	26	**#WE6**



Name	Function
I/O0~I/O7	DATA INPUTS/OUTPUTS The I/O pins are used to input command, address and data, and to output data during read operations. The I/O pins float to high-z when the chip is deselected or when the outputs are disabled.
CLE	COMMAND LATCH ENABLE The CLE input controls the activating path for commands sent to the command register. When active high, commands are latched into the command register through the I/O ports on the rising edge of the WE signal.
#CE0	Chip Enable Input .When #CEn is Low, the command input cycle becomes valid. When #CEn is High, all inputs are ignored.
#CE1	
#CE2	
#CE3	
#CE4	

Name	Function
#CE5	
#CE6	
#CE7	
ALE	ADDRESS LATCH ENABLE The ALE input controls the activating path for the address to the internal address registers. Addresses are latched on the rising edge of #WE with ALE high.
#REn	READ ENABLE The #REn input is the serial data-out control, and when active，drives the data onto the I/O bus. Data is valid t_{REA} after the falling edge of #RE which also increments the internal column address counter by one.
#WEn	WRITE ENABLE The #WEn input controls writes to the I/O port. Commands, address and data are latched on the rising edge of the #WE pulse.
#WP	WRITE PROTECT The #WP pin provides inadvertent write/erase protection during power transitions. The internal high voltage generator is reset when the #WP pin is active low.
#RB0	READY/BUSY OUTPUT The #R/Bn output indicates the status of the device operation. When low it indicates that a program, erase or random read operation is in process and returns to high state upon completion. It is an open drain output and does not float to high-z condition when the chip is deselected or when outputs are disabled.
#RB1	
#RB2	
#RB3	
#RB4	
#RB5	
#RB6	
#RB7	
VCC	POWER:VCC is the power supply for device.
VSS	GROUND

5. ELECTRICAL SPECIFICATIONS

5.1. Absolute Maximum Ratings

Characteristics	Symbol	Maximum ratings	Unit
Voltage on VCC supply relative to Vss	V_{CC}	-0.6 to +4.6	V
Voltage on any pin relative to Vss	V_{IN}	-0.6 to +4.6	V
Power Dissipation	P_D	2.0	W
Operating Temperature Range	T_{OPR}	-55~ +125	℃
Storage Temperature Range	T_{STG}	-65 to +150	℃

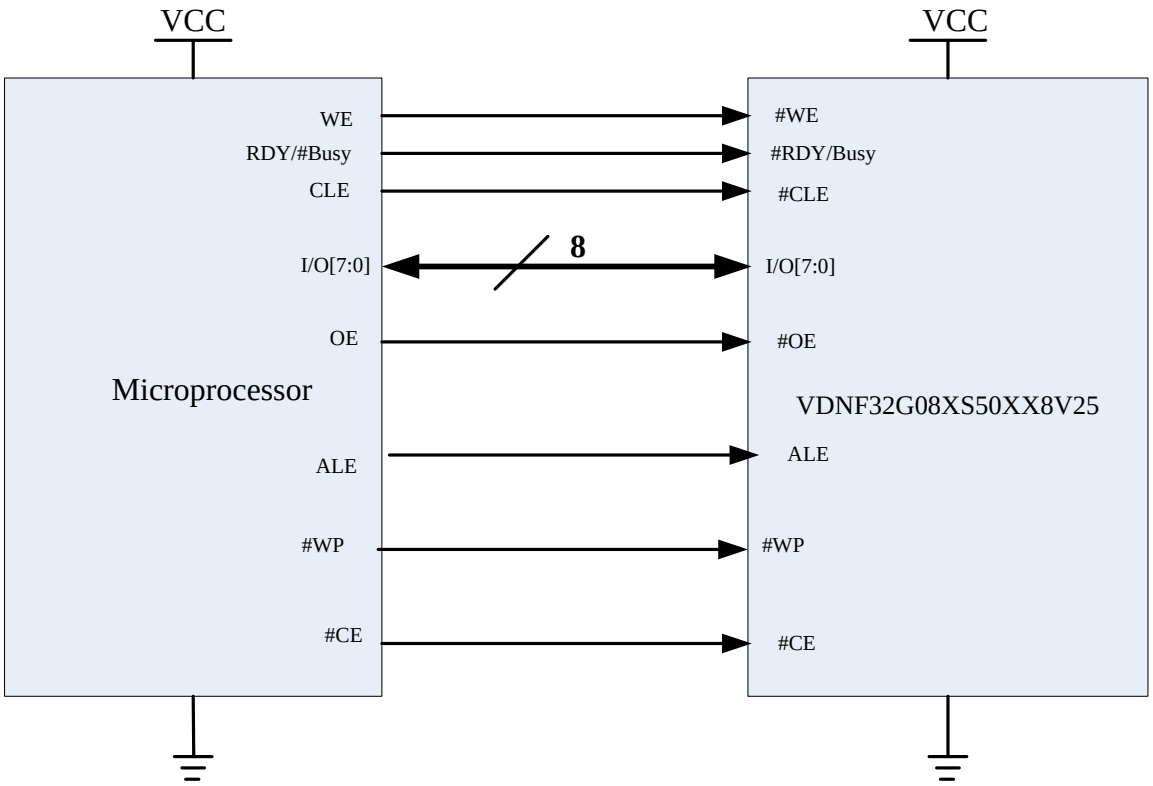
5.2. Recommended DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	2.7	3.3	3.6	V
Input high voltage	V_{IH}	V_{CC}×0.8	——	V_{CC}+0.3	V
Input low voltage	V_{IL}	-0.3	——	V_{CC}×0.2	V

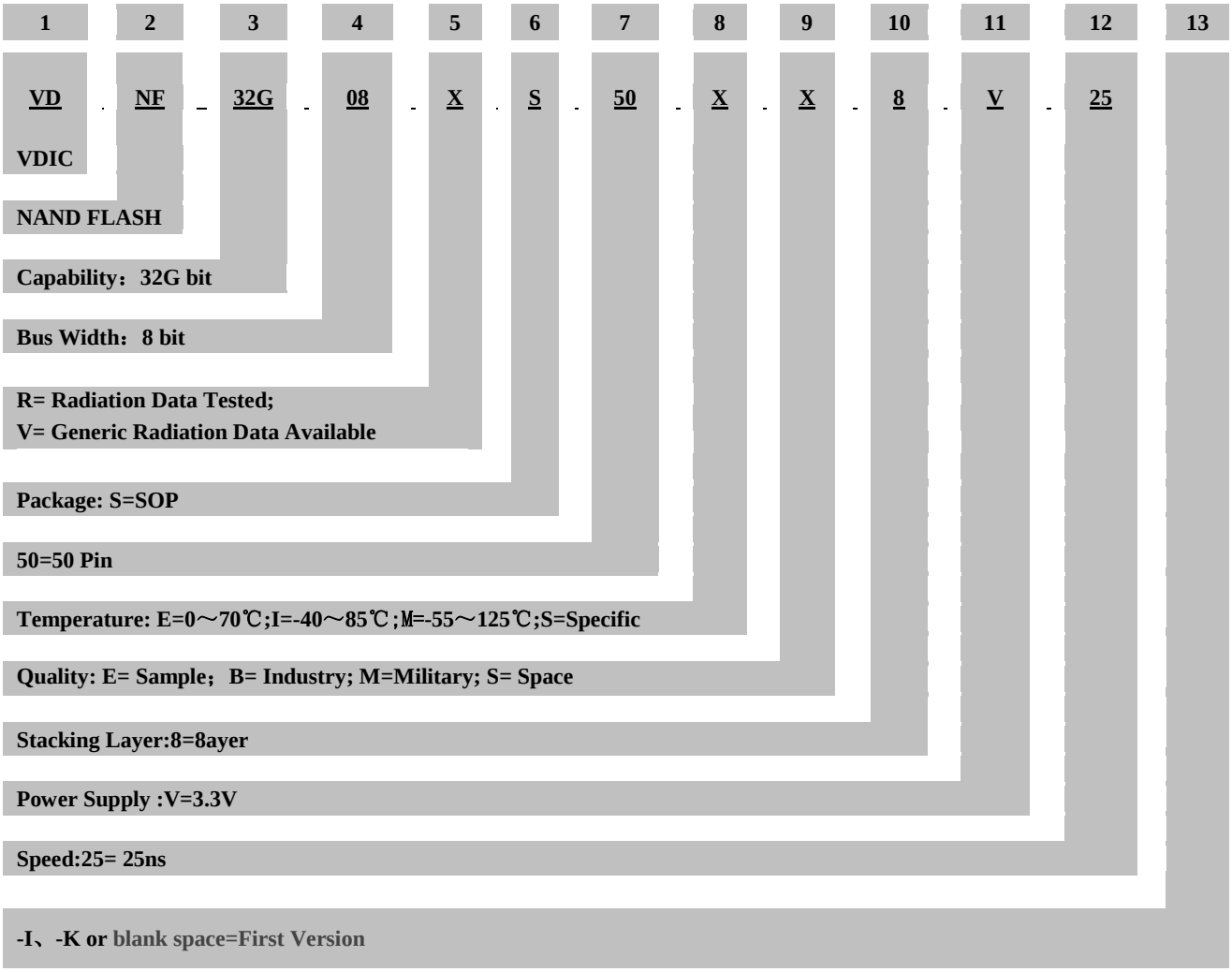
5.3. DC And Operating Characteristics

Parameter	Symbol	Test Conditions	Min	Max	Unit
Output voltage low level	V_{OL}	V_{CC}=3.6V I_{OL} =4mA	——	0.4	V
Output voltage high level	V_{OH}	V_{CC}=2.7V,I_{OH}= -4mA	2.4	——	V

6. Typical Application



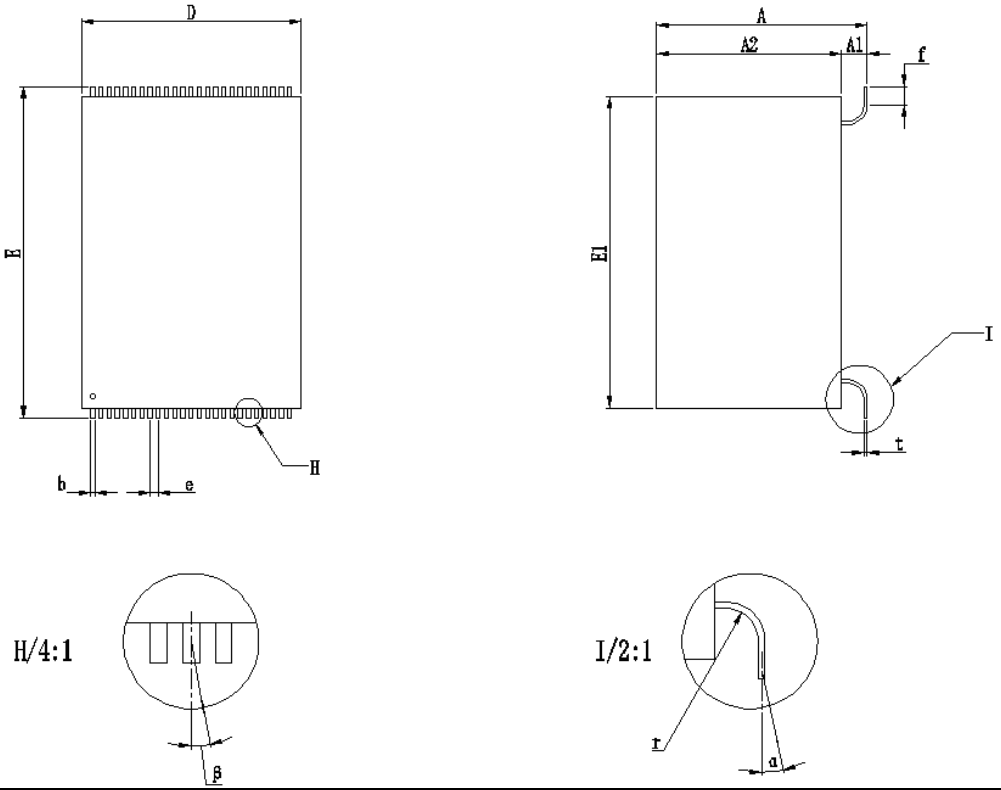
7. ORDERING INFORMATION



Part Number	Capacity (bit)	Bus Width (bit)	Radiation			Packaging	Temperature (℃)
			TID[1]	SEL[2]	SEU[3]		
VDNF32G08VS50EE8V25	32G	8	-	-	-	SOP50	0 ~ + 70
VDNF32G08VS50IB8V25	32G	8	-	-	-	SOP50	-40 ~ + 85
VDNF32G08VS50MB8V25	32G	8	-	-	-	SOP50	-55 ~ + 125
VDNF32G08VS50MM8V25	32G	8	-	-	-	SOP50	-55 ~ + 125
VDNF32G08RS50MS8V25	32G	8	>60	>62.5	1.3	SOP50	-55 ~ + 125

[1] TID: Total Dose（Krads(Si)）
[2] SEL: LET Threshold（Mev.cm2/mg）
[3] SEU:SEU Threshold （Mev.cm2/mg）

8. PACKAGE DIMENSIONS



	Min	Max
A	12.30	12.80
A2	11.10	11.50
D	13.30	13.70
E	19.80	20.20
E1	18.80	19.20
f	1.20	
b	0.25	
e	0.50	
r	1.00	
t	0.20	
α	≤3°	
β	≤3°	
Notes： 1. Unit：mm 2. A1= A - A2		

9. REVISION HISTORY

Revision	Date	Description of Change
A0	Nov 3,2015	First Created
A1	Mar 14,2016	Modified the PIN DESCRIPTIONS
A2	Aug 23,2016	Modified the ORDERING INFORMATION
A3	Jan 9,2017	Modified the PACKAGE DIMENSIONS
A4	Oct.25,2017	Changed company's name to Zhuhai Orbita Aerospace Science & Technology Co.，Ltd
A5	Mar 24,2018	Add or reduce chapters